

ABSTRACT OF THE DISCLOSURE

A semiconductor laser device includes a QW active layer structure including a $\text{Ga}_x\text{In}_{1-x}\text{As}_{1-y}\text{Sb}_y$ layer wherein $0.3 \leq 1-x$ and $0.003 \leq y \leq 0.008$, or a QW active layer structure including a $\text{Ga}_x\text{In}_{1-x}\text{As}_{1-y_1-y_2}\text{N}_{y_1}\text{Sb}_{y_2}$ layer wherein $0.3 \leq 1-x$, $0 < y_1 < 0.03$ and $0.002 \leq y_2 \leq 0.06$. The semiconductor laser device suppresses the three-dimensional epitaxial growth, and has superior optical characteristics including a low threshold current.

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